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(54) THREE-DIMENSIONAL MEMORY DEVICE WITH SELF-ALIGNED WORD LINE CONTACT VIA STRUCTURES AND METHOD OF MAKING THE SAME

(52) U.S. Cl. CPC ....... H10B 43/27 (2023.02); H01L 23/5226 (2013.01); *H10B* 43/10 (2023.02)

**ABSTRACT** 

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## Related U.S. Application Data

- Continuation-in-part of application No. 18/221,689, filed on Jul. 13, 2023.
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## **Publication Classification**

(51) **Int. Cl.** H10B 43/27 (2006.01)H01L 23/522 (2006.01)H10B 43/10 (2006.01) A three-dimensional memory device includes: an alternating stack of insulating layers and electrically conductive layers having stepped surfaces in a contact region; memory openings vertically extending through the alternating stack; memory opening fill structures located in the memory openings; a retro-stepped dielectric material portion overlying the stepped surfaces; and a layer contact assembly vertically extending through the retro-stepped dielectric material portion and through a subset of layers in the alternating stack and including: a dielectric pillar structure that is laterally surrounded by the subset of layers in the alternating stack; and a layer contact via structure including a cylindrical conductive material portion that vertically extends through the retro-stepped dielectric material portion and a downward-protruding tubular portion adjoined to a bottom end of the cylindrical conductive portion and having an annular

bottom surface that contacts an electrically conductive layer

